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		("SiO.sub.2" silica "silicon oxide") and	EPO; JPO;	00:31
	Į.	("stannic oxide" "tin oxide" "SnO.sub.2")	DERWENT	
		and (substrate near9 (sodium na)) and nm		
		and electron and particle and platinum		
,		and silver		
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1		("stannic oxide" "tin oxide" "SnO.sub.2")	DERWENT	
		and (substrate near9 (sodium na)) and nm		
		and particle and phosphorous		
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		("SiO.sub.2" silica "silicon oxide") and	EPO; JPO;	00:42
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		("stannic oxide" "tin oxide" "SnO.sub.2")	DERWENT	
		and (substrate near9 (sodium na)) and nm		
		and particle and phosphorus		
-	3	313/309-311,495-497.ccls. and	USPAT;	2003/04/07
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		and (substrate near9 (sodium na)) and nm		
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1		"4303917" "4325084").PN.		
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				03:52
-	1	(phosphorus with "sio.sub.2") and	USPAT;	2003/04/07
		electron and 313/309-311,495-497.ccls.	EPO; JPO;	07:49
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